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April 2025

FDD3N50NZ

N-Channel UniFETTM II MOSFET 500 V, 2.5 A, 2.5 Ω

Features

- $R_{DS(on)}$ = 2.1 Ω (Typ.) @ V_{GS} = 10 V, I_D = 1.25 A
- Low Gate Charge (Typ. 6.2 nC)
- Low C_{rss} (Typ. 2.5 pF)
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · ESD Imoroved Capability
- RoHS Compliant

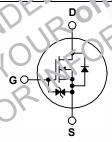
Applications

- LCD/LED/PDP TV
- Lighting
- · Uninterruptible Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET has the smallest on-state resistance among the plan MOS T, and also provides superior switching performant and Inher avalanche energy strength. In addition internal telescore ESD globy allows UniFET II MOSFE to mistancial 2kV halk surge stress. This device it if you uitable for switching power converter applications such as productor correction (PFC), flat panel display (in D) TV week, ATX and electronic lamp ballasts





Absolut Maxim m Ratings T_C = 25% unless other vise noted.

Sym. '	G CY	FDD3N50NZTM	Unit	
V, 3	Drain to Source Voltage	500	V	
V _{GS}	Gate to Source Initiage		±25	V
	Drain Current	- Continuous (T _C = 25°C)	2.5	Α
I _D Drain Current		- Continuous (T _C = 100°C)	1.5	^
I _{DM}	Drain Current	- Pulsed (Note 1)	10	Α
EAS	Single Pulsed Avalanche Energy (Note 2)		114	mJ
'AR	Avalanche Current (Note 1)		2.5	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	10	V/ns
D	Dower Dissipation	(T _C = 25°C)	40	W
P_D	Power Dissipation	- Derate Above 25°C	0.3	W/°C
T _J , T _{STG}	Operating and Storage Tempe	rature Range	-55 to +150	οС
Tı	Maximum Lead Temperature f	300	οС	

Thermal Characteristics

Symbol	Parameter	FDD3N50NZTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 90		C/VV

Package Marking and Ordering Information

Pai	t Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD	3N50NZTM	FDD3N50NZ	DPAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C	-	0.5	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	-	-	1	μА
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-		10	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±25 V, V _{DS} = 0 V		-	±10	μА

On Characteristics

V	GS(th)	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$.U		5.0	V
R	R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 1.25 A		2.1	2.5	Ω
g	FS	Forward Transconductance	V _{DS} = 20 V, I _D = 1.25 A		1.9	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	- 212 280	pF
Coss	Output Capacitance	V- 25 '/ _{GS} '0 V, - 30 4.	pF
C _{rss}	Reverse Transfer Capacitance	VIII 2.5 5	pF
Q _{g(tot)}	Total Gate Charge at 10V	$V_{DS} = 7 \text{ V}, I_D = 2.5 \text{ A}$	nC
Q _{gs}	Gate to Source Gate Charge	' _{GS} = 10 V - 1.4 -	nC
Q_{gd}	Gate to Drain "Miller" Cha	(Note 4) - 3.1 -	nC

Switching Characteristics

•		13.				
t _{d(on)}	Turn-On Del 11me		-	10	30	ns
t _r	Turn-On Ris Time $V_{DD} = 250 \text{ V}, I_D = 2.5 \text{ A}$		-	15	40	ns
$t_{d(off)}$	Ti' U. Dela, ime V _{GS} = 10 V, R _C , = 25 C.		- /	26	60	ns
t _f	T Time	(Note 4)	-	17	45	ns

Drain ur. Di di shara teristics

Is -	M. 'mum Continuous Drain to Source Diode Forward Current		-/-	-	2.5	Α
I _{SM}	Maximum Pulsed Drain o Source Dicae F	orward Current	-	-	10	Α
V _{SD}	Drain to Source Dioc'e Forward Vollage	V _{GS} = 0 V, I _{SD} = 2.5 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 2.5 A,	-	190	-	ns
Q _{rr}	Reverse Recovery Clarue	dI _F /dt = 100 A/μs	-	0.52	y -	μC

Nr les:

Reprititive rating: pulse-width limited by maximum junction temperature.

- ?. L = 36.6 mH, I $_{AS}$ = 2.5 A, V $_{DD}$ = 5 I V, $_{G}$ = 25 $_{\Omega}$, starting T $_{J}$ = 25°C.
- 3. $I_{SD} \le 2.5$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

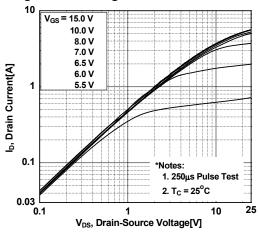


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

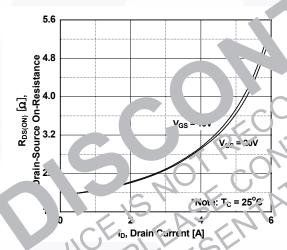


Figure 5. Capacitance Characteristics

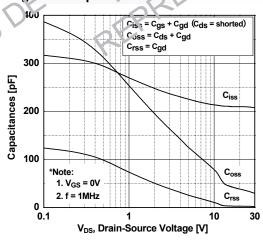
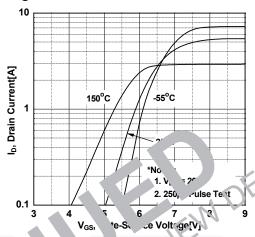


Figure 2. Transfer Characteristics



Variation vs. Source Current and Temperature

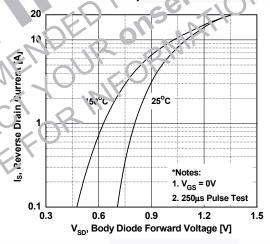
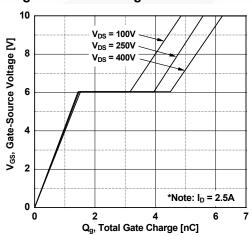


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

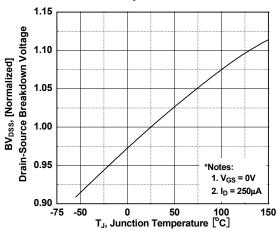


Figure 8. On-Resistance Variation vs. Temperature

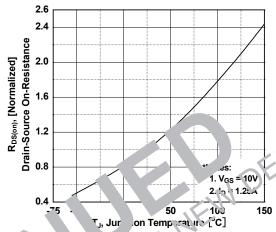
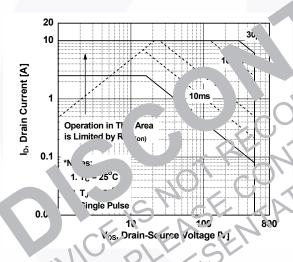


Figure 9. Maximum Safe Operating Area



igu.). Maximum Drain Gyrrent vs. Case Temperature

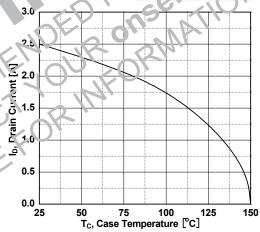
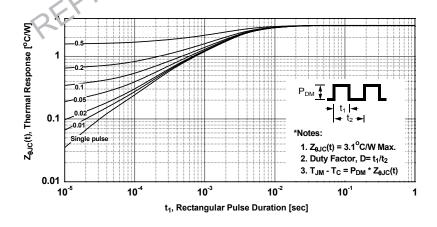


Figure 11. Transient Thermal Response Curve



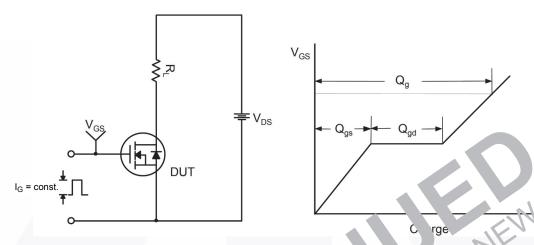


Figure 12. Gate Charge Test Circui. 3 W. 105 .m



Figure 13. Resistive Switching Test Circuit & Waveforms

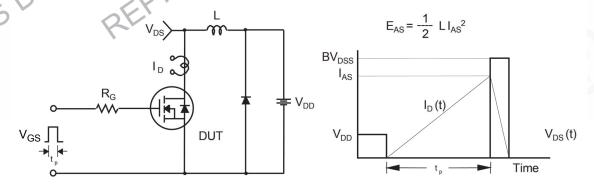


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

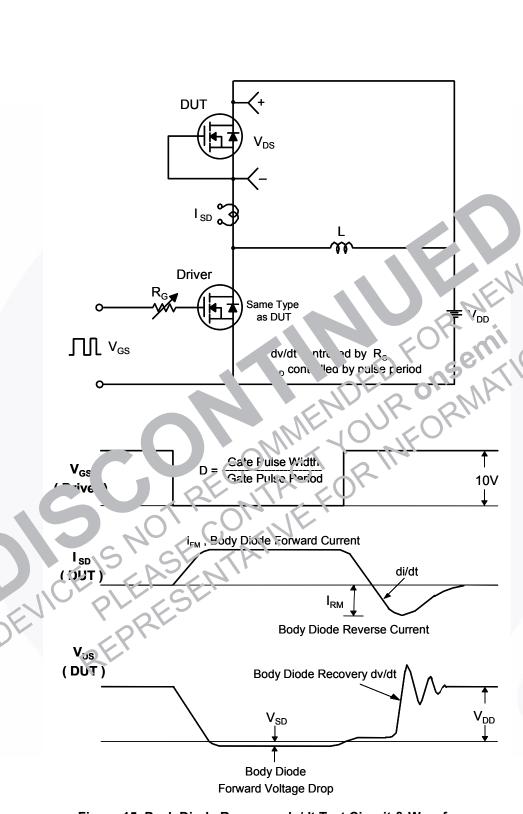


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

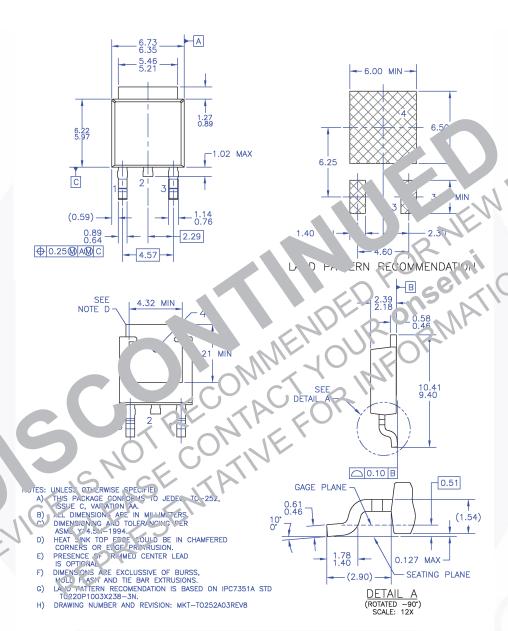


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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